

Atomic-scale Thermoelectric Refrigerator.

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This study proposes a thermoelectric cooling device based on an atomic-sized junction. Using first-principles approaches, the working conditions and coefficient of performance (COP) of an atomic junction as an electronic refrigerator are investigated. Quantum nature due to the size minimization offered by atomic-level control of properties facilitates electron cooling beyond the expectation of the conventional thermoelectric device theory. Our studies reveal that the 4-Al junction with $ZT=0.02$ could have refrigeration efficiency comparable to a bulk thermoelectric refrigerator with a ZT of an order of magnitude larger.

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I. INTRODUCTION

The transport properties of atomic-scale junctions are currently eliciting a tremendous wave of multidisciplinary scientific interest [1, 2]. This interest is motivated by the aspiration to develop new forms of electronic devices based on subminiature structures and to understand the fundamental properties of non-equilibrium transport in atomic-scale junctions. A growing number of studies are currently available to diversify the scopes of transport properties in molecular/atomic junctions, including current-voltage characteristics [3–7], inelastic electron tunneling spectroscopy (IETS) [8–16], shot noise [17–20], counting statistics [21], local heating [22, 23], and gate-controlled effects [24–28]. Substantial progress in experiment and theory has also been achieved [29–31].

Recently, considerable attention is being paid to thermopower of nanojunctions. Atomic scale thermoelectric junctions are gaining increased attention due to the recent measurements of Seebeck coefficient, defined as $S = dV/dT$, in metallic atomic/molecular junctions [32–35]. Measurements of Seebeck coefficient provide a useful experimental approach to exploring the electronic structure of the molecule bridging the electrodes [36]. These experiments inspire rapid development in the theory of thermoelectricity at the atomic and molecular scale [37–49].

Exploring the possibility of subminiature energy-conversion devices is scientifically and technologically important. Thermoelectric effects hybridize the electron and energy transport, which complicates the fundamental understanding for quantum transport of electron and energy under non-equilibrium conditions. Thermoelectric nanojunctions open new challenges for developing novel energy-conversion nano-devices, such as thermoelectric power generators and refrigerators at the atomic/molecular level. Methodologically, the scope of the research needs to extend through the utilization of unprecedented experiment and theory. Thus far, previous reports, focus only on the Seebeck coefficient (S) and the thermoelectric figure of merit (ZT) of nanojunctions. Little attempt is made to explore new forms of thermoelectric devices based on atomic-scale junctions [50, 51]. This project initiates research on the theory of working conditions and coefficient of performance (COP) in thermoelectric nano-refrigerator. It offers a key to understanding the nanoscale energy-conversion mechanism and may open a new path in exploring novel thermoelectric nano-devices.

The Seebeck coefficient is related closely to the magnitude and slope of transmission function near the chemical potentials. To have an efficient energy-conversion device, the thermoelectric junctions with large magnitudes of Seebeck coefficients and small magnitudes of thermal conductances are of key importance. Such systems are often characterized by sharp density of states (DOSs) near the chemical potentials and poor mechanical coupling between the nano-object and electrodes.

Compared with atomic-scale thermoelectric power generators [52], thermoelectric refrigerators require more stringent working conditions. In the bulk and mesoscopic system, the efficiency of a thermoelectric (TE) refrigerator is usually suppressed by the large work function and the overwhelmingly irreversible Joule heating. For example, the operation of a thermoelectric cooling device, such as a vacuum diode, is limited to very high temperatures due to its large potential barrier [53]. Recently, researchers have shown the prospect of operating thermoelectric refrigerators at room temperature using semiconductor heterojunctions to reduce the work function [54–57]. An alternative new approach to low temperature-operated thermoelectric refrigerators may be atomic-sized junctions, the extreme limit of device miniaturization.

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This study addresses the question of thermoelectric cooling based on an atomic junction operated at the applied bias $V_B < V_{onset}$, where V_{onset} is the onset bias of local heating. To enrich the understanding of thermoelectric cooling mechanism at the atomic level, we develop an analytical theory which offers more elaborate explanation of the working conditions, threshold bias, and behaviors of COP in thermoelectric nano-refrigerators. As an example, we investigate the thermoelectric cooling effects in the 4-Al junction as an electronic refrigerator with and without the thermal current carried by phonons using first-principles approaches. The atomic thermoelectric junction is marked by the reduced tunneling potential due to bridging atoms, the enhanced Seebeck coefficient due to a Px-Py sigma channel, the suppressed local heating due to discrete vibrational modes, and the reduced photon radiation due to small contact surface. Due to size minimization, these quantum natures remarkably facilitate efficient thermoelectric cooling effect beyond the expectations of the conventional thermoelectric device theory. Our calculations indicate that the novel thermoelectric nano-refrigerator is promising because it allows electronic nano-refrigerators to perform in a wide range of temperatures, even at temperatures under 100 K, which is a great improvement in comparison with the vacuum diode [53].

The cooling effect in thermoelectric nanojunctions could be destroyed by the adverse phonon's thermal current, which is likely to depend strongly on the detailed atomic structure of the full system especially in the contact region. To minimize the adverse effects imposed by the phonon's thermal current, we suggest creating a weak mechanical link between the nano-structured object and the electrodes while still allowing electrons to tunnel. Our theory reveals that the choice of a thermoelectric junction with a large Seebeck coefficient is of crucial importance to the design of nano-refrigerator. Widely diversified atomic-sized junctions may be achieved by manipulating the species of nano-structured objects and contact regions. Such manipulations may lead to a significant change in DOSs, consequently varying the Seebeck coefficients of nano-junctions. Atomic-level control of the contact region plays a primary role in yielding enhanced Seebeck coefficient and creating poor thermal contact. A full exploration of all possibilities in such an unknown system may open new opportunities and challenges in developing new forms of thermoelectric cooling devices at the atomic level.

The flow of the discussion in this paper is as follows. Firstly, we describe the details of density functional theory, theory of thermoelectricity, and theory of thermoelectric nano-refrigerator in the absence and presence of phonon's thermal current in section II. **Theoretical Methods**. In section III. **Results and discussion**, we discuss the thermoelectric properties of 4-Al atomic junctions, and subsequently discuss the onset bias, working conditions, and COP of thermoelectric nano-refrigerators. We then summarize our findings in section IV. **Conclusions**.

II. THEORETICAL METHODS

The theories presented in the following subsections are general to any atomic/molecular junction that utilizes tunneling as the major transport mechanism, provided that the applied bias is much smaller than the onset bias of local heating. In the subsection **A. Density Functional Theory**, we present an introduction of the density-functional theory (DFT). In the subsection **B. Theory of Thermoelectricity**, we present the theory to calculate the Seebeck coefficient, electric conductance, electron's thermal conductance, phonon's thermal conductance, and thermoelectric figure of merit (ZT). In the subsection **C. Theory of Thermoelectric Refrigerator**, we present the theory for the rate of thermal energy removal from the cold-temperature reservoir, the working condition for thermoelectric refrigeration, and the coefficient of performance for the atomic-scale thermoelectric refrigerator with and without the presence of thermal current of the phonon.

A. Density Functional Theory

The electric current, electron's thermal current, and Seebeck coefficient are calculated in a truly atomic-scale junction in terms of the effective single-particle wave-functions obtained self-consistently within the DFT. In this subsection, we present a brief introduction of how to calculate the electric current and the electron's thermal current carried by the electron transport in the DFT framework. We picture a nanoscale junction as formed by two semi-infinite electrodes held apart at a fixed distance with a nano-structured object bridging the gap between them. The full Hamiltonian of the system is $H = H_0 + V$, wherein H_0 is the Hamiltonian due to the bare electrodes and V is the scattering potential of the nano-structured object.

First, we calculate the wave functions of the bare electrodes with an applied bias $V_B = (\mu_R - \mu_L)/e$, where $\mu_{L(R)}$ is the chemical potential deep in the left (right) electrode. The unperturbed wave functions of the bare electrodes have the form, $\Psi_{E\mathbf{K}_\parallel}^{0,L(R)}(\mathbf{r}) = e^{i\mathbf{K}_\parallel \cdot \mathbf{R}} \cdot u_{E\mathbf{K}_\parallel}^{L(R)}(z)$, where $u_{E\mathbf{K}_\parallel}^{L(R)}(z)$ describes the electrons incident from the left (right) electrode before the inclusion of the nano-structured object. The equation $u_{E\mathbf{K}_\parallel}^{L(R)}(z)$ is calculated by solving the Schrödinger

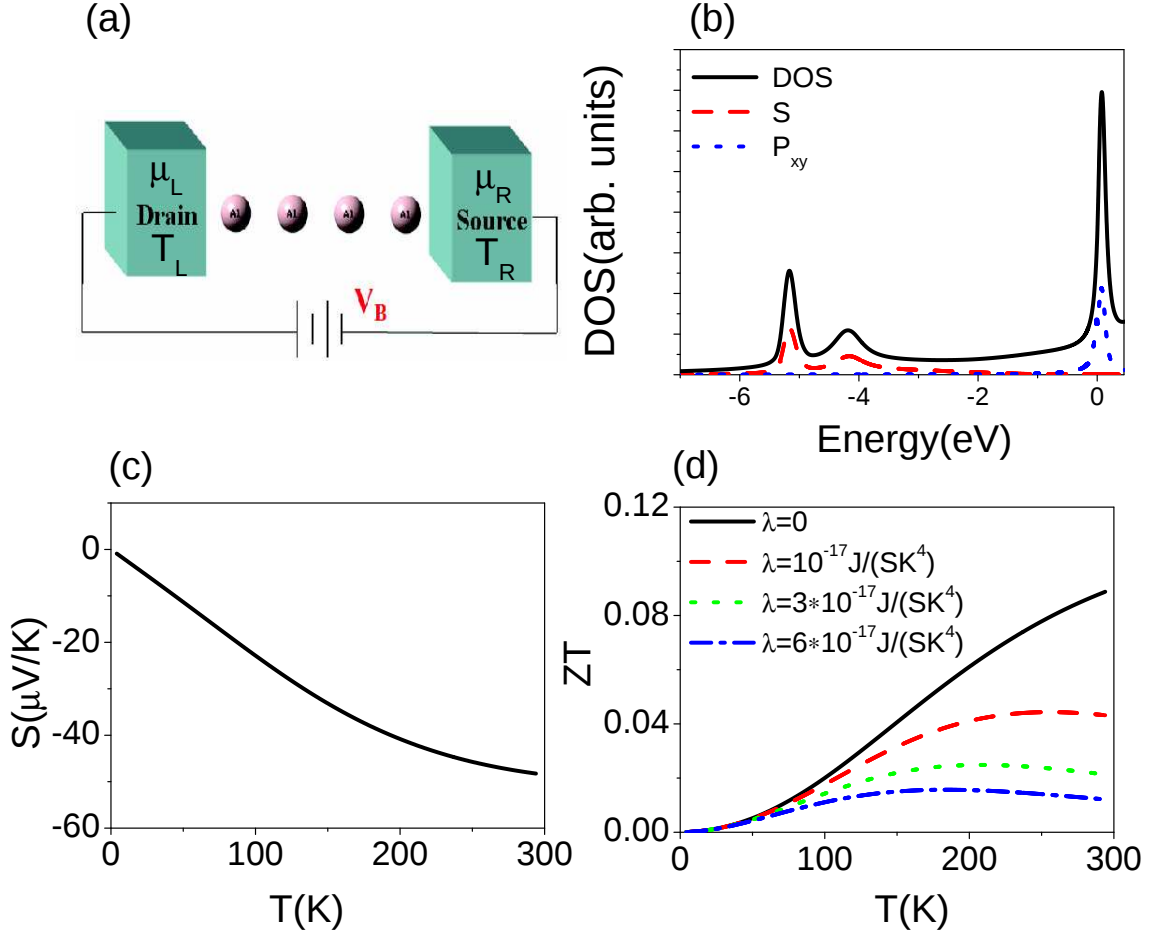


FIG. 1: (Color online) (a) Scheme of the 4 – Al atomic junction with different temperatures $T_{L(R)}$ and chemical potentials $\mu_{L(R)}$. The Al-jellium distance is about 2.5 a.u. and the Al – Al bond distance is about 6.3 a.u.; (b) Density of state and projected density of states of the 4 – Al junction; (c) Seebeck coefficient vs. temperature of the 4 – Al junction; and (d) ZT vs. T with the phonon's thermal current for various values of λ .

equation and Poisson equations iteratively until self-consistency is obtained. Note that $u_{E\mathbf{K}_{\parallel}}^R(z)$ satisfies the following boundary condition:

$$u_{E\mathbf{K}_{\parallel}}^R(z) = (2\pi)^{-\frac{3}{2}} \times \begin{cases} \frac{1}{\sqrt{k_R}}(e^{-ik_R z} + R e^{ik_R z}), & z \rightarrow \infty, \\ \frac{1}{\sqrt{k_L}}T e^{-ik_L z}, & z \rightarrow -\infty, \end{cases} \quad (1)$$

where $\mathbf{K}_{\parallel}$ is the electron momentum in the plane parallel to the electrode surfaces, and z is the coordinate parallel to the direction of the current. The condition of energy conservation gives $\frac{1}{2}k_R^2 = E - \frac{1}{2}|\mathbf{K}_{\parallel}|^2 - v_{eff}(\infty)$ and $\frac{1}{2}k_L^2 = E - \frac{1}{2}|\mathbf{K}_{\parallel}|^2 - v_{eff}(-\infty)$, where $v_{eff}(z)$ is the effective potential comprising the electrostatic and exchange-correlation potentials.

The nano-structured object is considered in the scattering approaches. The scattering wave functions of the entire system are calculated by solving the Lippmann-Schwinger equation iteratively until self-consistency is obtained,

$$\Psi_{E\mathbf{K}_{\parallel}}^{L(R)}(\mathbf{r}) = \Psi_{E\mathbf{K}_{\parallel}}^{0,L(R)}(\mathbf{r}) + \int d^3\mathbf{r}_1 \int d^3\mathbf{r}_2 G_E^0(\mathbf{r}, \mathbf{r}_1) V(\mathbf{r}_1, \mathbf{r}_2) \Psi_{E\mathbf{K}_{\parallel}}^{L(R)}(\mathbf{r}_2), \quad (2)$$

where $\Psi_{E\mathbf{K}_{\parallel}}^{L(R)}(\mathbf{r})$ stands for the effective single-particle wave functions of the entire system, which also represents the electrons with energy E incident from the left (right) electrode. The potential $V(\mathbf{r}_1, \mathbf{r}_2)$ that the electrons experience when they scatter through the nanojunction is

$$V(\mathbf{r}_1, \mathbf{r}_2) = V_{ps}(\mathbf{r}_1, \mathbf{r}_2) + \left\{ (V_{xc}[n(\mathbf{r}_1)] - V_{xc}[n_0(\mathbf{r}_1)]) + \int d\mathbf{r}_3 \frac{\delta n(\mathbf{r}_3)}{|\mathbf{r}_1 - \mathbf{r}_3|} \right\} \delta(\mathbf{r}_1 - \mathbf{r}_2), \quad (3)$$

where $V_{ps}(\mathbf{r}_1, \mathbf{r}_2)$ is the electron-ion interaction potential represented with pseudopotential; $V_{xc}[n(\mathbf{r})]$ is the exchange-correlation potential calculated at the level of the local-density approximation; $n_0(\mathbf{r})$ is the electron density for the pair of biased bare electrodes; $n(\mathbf{r})$ is the electron density for the total system; and $\delta n(\mathbf{r})$ is their difference. The quantity G_E^0 is the Green's function for the bare electrodes. The wavefunctions that achieve self-consistency in the DFT framework in plane wave basis are applied to calculate the electric current, and the electron's thermal current.

These right- and left-moving wave functions weighed with the Fermi-Dirac distribution function according to their energies and temperatures are applied to calculate the electric current as

$$I(\mu_L, T_L; \mu_R, T_R) = \frac{e\hbar}{mi} \int dE \int d\mathbf{r}_\perp \int d\mathbf{K}_\parallel \left[f_E(\mu_R, T_R) I_{EE, \mathbf{K}_\parallel}^{RR}(\mathbf{r}) - f_E(\mu_L, T_L) I_{EE, \mathbf{K}_\parallel}^{LL}(\mathbf{r}) \right], \quad (4)$$

where $I_{EE', \mathbf{K}_\parallel}^{RR(LL)}(\mathbf{r}) = \left[\Psi_{E, \mathbf{K}_\parallel}^{R(L)}(\mathbf{r}) \right]^* \nabla \Psi_{E', \mathbf{K}_\parallel}^{R(L)}(\mathbf{r}) - \nabla \left[\Psi_{E, \mathbf{K}_\parallel}^{R(L)}(\mathbf{r}) \right]^* \Psi_{E', \mathbf{K}_\parallel}^{R(L)}(\mathbf{r})$ and $d\mathbf{r}_\perp$ represents an element of the electrode surface. Here, we assume that the left and right electrodes are independent electron reservoirs, with the population of the electron described by the Fermi-Dirac distribution function, $f_E(\mu_{L(R)}, T_{L(R)}) = 1/\{\exp[(E - \mu_{L(R)})/(k_B T_{L(R)})] + 1\}$, where $\mu_{L(R)}$ and $T_{L(R)}$ are the chemical potential and the temperature in the left (right) electrode, respectively. More detailed descriptions of theory can be found in Refs. [4, 64, 65].

The above expression can be cast in a Landauer-Büttiker formalism:

$$I(\mu_L, T_L; \mu_R, T_R) = \frac{2e}{h} \int dE \tau(E) [f_E(\mu_R, T_R) - f_E(\mu_L, T_L)], \quad (5)$$

where $\tau(E) = \tau^R(E) = \tau^L(E)$ is a direct consequence of the time-reversal symmetry, and $\tau^{R(L)}(E)$ is the transmission function of the electrons with energy E incident from the right (left) electrode,

$$\tau^{R(L)}(E) = \frac{\pi \hbar^2}{mi} \int d\mathbf{r}_\perp \int d\mathbf{K}_\parallel I_{EE, \mathbf{K}_\parallel}^{RR(LL)}(\mathbf{r}). \quad (6)$$

There is an analog between the electric current and electron's thermal current. The flow of elections can also transport energy. The electron's thermal current, defined as the rate at which thermal energy flows from the right (into the left) electrode, is

$$J_{el}^{R(L)}(\mu_L, T_L; \mu_R, T_R) = \frac{2}{h} \int dE (E - \mu_{L(R)}) \tau(E) [f_E(\mu_R, T_R) - f_E(\mu_L, T_L)]. \quad (7)$$

B. Theory of Thermoelectricity

In this subsection, we present the theory to calculate the zero-bias electric conductance, Seebeck coefficient, and electron's thermal conductance for a thermoelectric nanojunction. These quantities have been calculated in terms of the effective single-particle wave-functions obtained self-consistently within the static density-functional theory in truly atomic-scale junction.

We assume that the left and right electrodes serve as independent temperature reservoirs. The population of electrons in the left (right) electrode is described by the Fermi-Dirac distribution function, $f_E(\mu_{L(R)}, T_{L(R)}) = 1/\{\exp[(E - \mu_{L(R)})/(k_B T_{L(R)})] + 1\}$, where the chemical potentials are $\mu_R = \mu_L = \mu$ (i.e., at zero external bias). Let us now consider an extra infinitesimal current induced by an additional infinitesimal temperature (dT) and voltage (dV) across the junctions in an open circuit. The current induced by dT and dV are $(dI)_T = I(\mu, T; \mu, T + dT)$ and $(dI)_V = I(\mu, T; \mu + dV, T)$, respectively, where $I(\mu, T; \mu, T + dT)$ and $I(\mu, T; \mu + dV, T)$ are given by Eq. (5). Suppose that the current cannot actually flow in an open circuit, thus, $(dI)_T$ counterbalances $(dI)_V$. In other words, the extra net current is zero,

$$dI = I(\mu, T; \mu + edV, T + dT) \approx (dI)_T + (dI)_V = 0. \quad (8)$$

The Fermi-Dirac distribution function in Eq. (8) can be expanded up to the first order in dT and dV , and we obtain the Seebeck coefficient (defined by $S = dV/dT$),

$$S(\mu, T) = -\frac{1}{eT} \frac{K_1(\mu, T)}{K_0(\mu, T)}, \quad (9)$$

where

$$K_n(\mu, T) = - \int dE \tau(E) (E - \mu)^n \frac{\partial f_E(\mu, T)}{\partial E}. \quad (10)$$

The Seebeck coefficient in the low-temperature regime can be obtained by expanding $K_n(\mu, T)$ to the lowest order in temperatures through the Sommerfeld expansion, that is, $K_0 \approx \tau(\mu)$, $K_1 \approx [\pi^2 k_B^2 \tau'(\mu)/3]T^2$, and $K_2 \approx [\pi^2 k_B^2 \tau(\mu)/3]T^2$. The Seebeck coefficient up to the lowest order in temperature is

$$S \approx \alpha T, \quad (11)$$

where $\alpha = -\pi^2 k_B^2 \frac{\partial \tau(\mu)}{\partial E} / (3e\tau(\mu))$. The Seebeck coefficient is positive (negative) when the slope of transmission function is negative (positive), which is closely related to the transmission function near the chemical potentials. We note that the Seebeck coefficient can be optimized via the gate voltage which shifts the DOSs.

The electron's thermal current is the energy current carried by electrons traveling between electrodes driven by dT and dV . Analogous to the extra current given by Eq. (8), the extra electron's thermal current is

$$dJ_{el} = (dJ_{el})_T + (dJ_{el})_V. \quad (12)$$

where $(dJ_{el})_T = J_{el}(\mu, T; \mu, T + dT)$ and $(dJ_{el})_V = J_{el}(\mu, T; \mu + edV, T)$ are the fractions of electron's thermal current driven by dT and dV , respectively. Note that dV is generated by the Seebeck effect according to the temperature difference dT . Both $J_{el}(\mu, T; \mu, T + dT)$ and $J_{el}(\mu, T; \mu + edV, T)$ can be calculated using Eq. (7).

Given that we define the electron's thermal conductance as $k_{el} = dJ_{el}/dT$, the electron's thermal conductance k_{el} can be decomposed into two components:

$$\kappa_{el}(\mu, T) = \kappa_{el}^T(\mu, T) + \kappa_{el}^V(\mu, T), \quad (13)$$

where $\kappa_{el}^T = (dJ_{el})_T/dT$ and $\kappa_{el}^V = (dJ_{el})_V/dT$. We note that κ_{el}^T and κ_{el}^V are the portions of the electron's thermal conductance driven by dT and dV , respectively. Analogous to Eq. (9), κ_{el}^T and κ_{el}^V can be expressed by Eq. (10):

$$\kappa_{el}^T(\mu, T) = \frac{2}{h} \frac{K_2(\mu, T)}{T}, \quad (14)$$

and

$$\kappa_{el}^V(\mu, T) = \frac{2e}{h} K_1(\mu, T) S(\mu, T). \quad (15)$$

One should note that $\kappa_{el}^V = 0$ if the Seebeck coefficient of the system is zero because dV is zero.

In the low-temperature regime, κ_{el}^T and κ_{el}^V can be expanded to the lowest order in temperatures using the Sommerfeld expansion:

$$\kappa_{el}^V \approx \beta_V T^3 \text{ and } \kappa_{el}^T \approx \beta_T T, \quad (16)$$

where $\beta_V = -2\pi^4 k_B^4 [\tau'(\mu)]^2 / (9h\tau(\mu))$ and $\beta_T = 2\pi^2 k_B^2 \tau(\mu) / (3h)$. In the above expansions, we also applied the following approximations: $K_1(\mu, T) \approx [\pi^2 k_B^2 \tau'(\mu)/3]T^2$, $K_2(\mu, T) \approx [\pi^2 k_B^2 \tau(\mu)/3]T^2$, and Eq. (11). In the low-temperature regime, κ_{el}^T dominates the electron's thermal current. Thus $\kappa_{el} \approx \kappa_{el}^T$ is linear in T , that is,

$$\kappa_{el}(\mu, T) \approx \beta_T T. \quad (17)$$

At zero bias, the electric conductance can be expressed as

$$\sigma(T) = \frac{2e^2}{h} \int dE f_E(\mu, T) [1 - f_E(\mu, T)] \tau(E) / (k_B T). \quad (18)$$

In the low-temperature regime, the zero-bias conductance is usually insensitive to temperatures if tunneling is the major transport mechanism.

Thus far, the physical quantities (S , σ , and κ_{el}) previously discussed are related to the propagation of electrons. The heat current carried by phonon may occur in a real system. The phonon's thermal current, which is driven by the temperature difference ΔT , flows from the hot reservoir into the cold reservoir. To determine the impact of the phonon's thermal current on refrigeration, the weak link model is chosen to describe it. The weak link model assumes that the nanojunction is a weak elastic link with a given stiffness K that can be evaluated from total energy calculations or from experimental measurement [60]. Two metal electrodes are regarded as the macroscopic bodies under their thermodynamic equilibrium, and are taken as ideal thermal conductors. To the leading order in the strength of the weak link, the phonon's thermal current (J_{ph}) via elastic phonon scattering is,

$$J_{ph} = \frac{2\pi K^2}{\hbar} \int_0^\infty dE E N_L(E) N_R(E) [n_L(E) - n_R(E)], \quad (19)$$

where $K = AY/l$ is the stiffness of the weak elastic link; Y is the Young's modulus of the junction; A is the cross-section; l is the length of the nano-structured object as the weak elastic link bridging the electrodes; $N_{L(R)}(E)$ is the spectral density of phonon states at the left (right) electrode surface which is measurable by experiments; and $n_{L(R)} \equiv 1/(e^{E/K_B T_{L(R)}} - 1)$ is the Bose-Einstein distribution function. In the long wave length limit, the spectral density of surface phonon is given by $N_{L(R)}(E) \approx CE$. The phonon's thermal conductance defined as $\kappa_{ph} = \Delta J_{ph}/\Delta T$ as $\Delta T \rightarrow 0$, is

$$\kappa_{ph} = [J_{ph}(T_L + \frac{\Delta T}{2}, T_R - \frac{\Delta T}{2}) - J_{ph}(T_L, T_R)]/\Delta T. \quad (20)$$

Expanding the Bose-Einstein distribution function in $J_{ph}(T_L + \frac{\Delta T}{2}, T_R - \frac{\Delta T}{2})$ to the first order of ΔT , we obtain the phonon's thermal conductance:

$$\kappa_{ph} = \frac{\pi K^2 C^2}{\hbar} \int_0^\infty dE E^3 \sum_{i=L,R} \frac{\partial n_i(E)}{\partial T_i}. \quad (21)$$

When $T_R \approx T_L = T$, then Eq. (21) is reduced to,

$$\kappa_{ph} = \frac{2\pi K^2 C^2}{\hbar} \int_0^\infty dE E^3 \frac{\partial n(E)}{\partial T}. \quad (22)$$

where $n = 1/[e^{E/(k_B T)} - 1]$.

The efficiency of thermoelectric nano-devices is conventionally described by the thermoelectric figure of merit ZT , which depends on the following physical factors: Seebeck coefficient (S), electric conductance (σ), electron's thermal conductance (κ_{el}), and phonon's thermal conductance (κ_{ph}). ZT is defined as

$$ZT = \frac{S^2 \sigma}{\kappa_{el} + \kappa_{ph}} T, \quad (23)$$

where S , σ , κ_{el} , and κ_{ph} can be numerically calculated using Eqs. (9), (18), (13), and (22), respectively. When ZT tends to infinity, the thermoelectric efficiency of nanojunctions will reach Carnot efficiency.

C. Theory of Thermoelectric Refrigerator

In this subsection, we present the thermoelectric cooling device theory at atomic scale. The left- and right-electrodes are assumed to be independent electron reservoirs, respectively, with the electron's population described by the Fermi-Dirac distribution function, respectively. The left (right) electrode serves as the hot (cold) temperature reservoir with temperature $T_R = T_C$ ($T_L = T_H = T_C + \Delta T$) and the phonon's population is described by Bose-Einstein distribution function. We consider the nanojunction connecting to an external battery with bias $V_B = (\mu_R - \mu_L)/e$, which drives the electrons flowing from the right- to left-electrodes. The thermal current carried by the electron traveling between two electrodes is given by Eq. (7). It should be noted that

$$J_{el}^R(\mu_L, T_L; \mu_R, T_R) + I(\mu_L, T_L; \mu_R, T_R) V_B = J_{el}^L(\mu_L, T_L; \mu_R, T_R), \quad (24)$$

which is due to the energy conservation, where $I(\mu_L, T_L; \mu_R, T_R)$ is the current given by Eq. (5). Equation (24) states that it consumes electric energy to take heat from the right (cold) into left (hot) reservoir. Thus, the thermoelectric junction can be regarded as an electronic cooling device when $J_{el}^R > 0$, which states that the thermoelectric junction is capable of removing heat from the cold reservoir.

A measure of a refrigerator's performance is the ratio of the rate of heat removed from the cold reservoir to the electric power done on the system. The ratio is called the coefficient of performance (COP):

$$\eta = \frac{J_{el}^R}{IV_B} = \frac{J_{el}^R}{|J_{el}^R - J_{el}^L|}, \quad (25)$$

where V_B is the bias applied across the nanojunction, I is the electric current, and J_{el}^R is the rate of thermal energy removed from the cold reservoir. The thermoelectric junction as a nano-refrigerator is working when $J_{el}^R > 0$ (and thus $\eta > 0$).

1. Properties of Thermoelectric Refrigerator in the Absence of the Phonon's Thermal Current

In the following, we develop an analytical theory to gain insight into the fundamentals of the cooling effect in the thermoelectric nanojunction. We apply the Sommerfeld expansion to $J_{el}^R(\mu_L, T_L; \mu_R, T_R)$ and obtain,

$$J_{el}^R \approx \frac{\pi^2 k_B^2}{3h} [\tau(\mu_L)(T_R^2 - T_L^2) + \tau'(\mu_L)(\mu_R - \mu_L)(T_R^2 + T_L^2)] - \frac{1}{h} [\tau(\mu_L)(\mu_R - \mu_L)^2] - \frac{1}{3h} [\tau'(\mu_L)(\mu_R - \mu_L)^3], \quad (26)$$

where we use the following relations: $\tau(E) \approx \tau(\mu_L) + \tau'(\mu_L)(E - \mu_L)$, $\tau(\mu_R) \approx \tau(\mu_L) + \tau'(\mu_L)(\mu_R - \mu_L)$, $T_L = T_R + \Delta T$, $\int_{\mu_L}^{\mu_R} (E - \mu_R) dE = -\frac{1}{2}(\mu_R - \mu_L)^2$, $\int_{\mu_L}^{\mu_R} (E - \mu_L)(E - \mu_R) dE = -\frac{1}{6}(\mu_R - \mu_L)^3$, and $\mu_R - \mu_L = eV_B$. When $\Delta T \ll T_R$, Equation (26) can be expressed as a polynomial of V_B :

$$J_{el}^R = -a + bV_B - cV_B^2 - dV_B^3, \quad (27)$$

where $a = 2\pi^2 k_B^2 \tau(\mu) T_R \Delta T / (3h)$, $b = 2e\pi^2 k_B^2 \tau'(\mu) T_R^2 / (3h)$, $c = e^2 \tau(\mu) / h$, and $d = e^3 \tau'(\mu) / (3h)$. The above equation is convenient for analytical exploration of the properties of thermoelectric nano-refrigerators.

A thermoelectric nano-refrigerator functions only when the maximum value of the electron's thermal current is positive, that is, $(J_{el}^R)_{\max} > 0$. In a small bias regime, the term V_B^3 can be neglected in Eq. (27), i.e., $J_{el}^R \approx -a + bV_B - cV_B^2$. In this case, the working condition of nano-refrigerator is given by $(J_{el}^R)_{\max} = (-4ac + b^2)/(4c) > 0$, which yields the criterion for the existence of electronic cooling

$$-S > \sqrt{\frac{2\pi^2 k_B^2}{3e^2} \left(\frac{\Delta T}{T_R} \right)}, \quad (28)$$

where $S = -\frac{\pi^2 k_B^2}{3e} \frac{\tau'(\mu)}{\tau(\mu)} T_R$ is the Seebeck coefficient of the nanoscale junction [48].

For a given T_R and a given temperature difference ΔT , $J_{el}^R(V_B)$ is a function of bias V_B . We observe that J_{el}^R is negative at $V_B = 0$, and thus a lower limit of bias (denoted as V_{th}^{el}) is needed. The threshold bias is defined as the smallest positive solution of $J_{el}^R(V_B) = 0$. For $V_B > V_{th}^{el}$, $J_{el}^R > 0$ and thermoelectric cooling effect exists. V_{th}^{el} has a very small value; hence, we keep the terms up to $O(V_B)$ in Eq. (27), i.e., $J_{el}^R(V_B) \approx -a + bV_B$. In this simple case, the threshold bias $V_{th}^{el} \approx a/b$ is derived from $J_{el}^R(V_{th}^{el}) = 0$, from which we obtain,

$$V_{th}^{el} = -\frac{\pi^2 k_B^2}{3e^2 S} \Delta T, \quad (29)$$

where we have assumed $\Delta T \ll T_R$. Eq. (29) shows that the threshold bias V_{th}^{el} is independent of T_R and increases as ΔT increases.

We note that J_{el}^R is a function of bias V_B , T_R , and ΔT . For a given bias V_B and a given temperature difference ΔT , J_{el}^R is a function of T_R . We observe that there is a lower limit of temperatures when the thermoelectric refrigerator is working. The onset temperature for refrigeration effect, denoted as T_{op} , is defined by $J_{el}^R(T_{op}) = 0$. The nano-refrigerator is not functioning ($J_{el}^R(T_R) < 0$) when $T_R < T_{op}$. Especially, $J_{el}^R(T_R)$ can be expressed as a polynomial of T_R , derived from Eq. (26). If the Seebeck coefficient is sufficiently large and we neglect the terms higher than $O(T_R^2)$, the threshold operation temperature T_{op} can be calculated analytically by solving the polynomial $J_{el}^R(T_R) = 0$, which gives:

$$T_{op} = \frac{1}{2} [\alpha/V_B + \sqrt{(\alpha/V_B)^2 + \beta V_B}], \quad (30)$$

where $\alpha = \frac{\tau(\mu)\Delta T}{\tau'(\mu)e}$ and $\beta = \frac{6e\tau(\mu)}{\pi^2 k_B^2 \tau'(\mu)}$. Equation (30) shows that T_{op} increases as ΔT and V_B increase, respectively. When $\Delta T = 0$, $\alpha = 0$ and Eq. (30) approaches to

$$(T_{op})_{\min} \approx \sqrt{\frac{V_B T_R}{-2S}}. \quad (31)$$

Equation (31) shows that T_{op} approaches to the lower limit $(T_{op})_{\min}$ as $\Delta T \rightarrow 0$, where $(T_{op})_{\min}$ increases as $V_B \cdot T_R$ increases.

We now turn to investigate the COP of the thermoelectric cooling device. When V_B is small, $J_{el}^L - J_{el}^R = IV_B \approx \sigma V_B^2$. In this case, the COP is in the following form,

$$\eta^{el} \approx \frac{J_{el}^R}{\sigma V_B^2}, \quad (32)$$

where $J_{el}^R(V_B)$ is a polynomial of V_B given by Eq. (25). The applied biases considered in this study are small, hence we can consider $J_{el}^R(V_B)$ [given by Eq. (27)] up to $O(V_B)$. Thus, Eq. (32) takes the form,

$$\eta^{el} = \frac{-a + bV_B}{\sigma V_B^2}. \quad (33)$$

The maximum value of COP (denoted as $\eta_{\max}^{el}$) occurs at $\eta'(V_{\max}^{\eta}) = 0$, which gives

$$\eta_{\max}^{el} = \frac{3e^2 S^2 T_R}{4\pi^2 k_B^2 \Delta T} - \frac{1}{2}, \quad (34)$$

where the maximum value of η^{el} occurs at bias $V_B = V_{\max}^{\eta}$, where

$$V_{\max}^{\eta} \approx 2V_{th}^{el}, \quad (35)$$

where V_{th}^{el} is given by Eq. (29). Concluding from Eqs. (29) and (34), the refrigeration effect is triggered at around $V_B = V_{th}^{el}$ and optimized around $V_B = 2V_{th}^{el}$.

2. Properties of Thermoelectric Refrigerator in the Presence of the Phonon's Thermal Current

Phonon's thermal current is an adverse effect to thermoelectric refrigeration because it heats up cold electrodes. To realize the impact of this adverse effect to refrigeration, we consider the weak-link model suitable for describing the heat transport for two thermal reservoirs connected by a weak elastic link [60]. In the low-temperature regime, Eq. (21) can be expanded up to the lowest order in temperatures,

$$J_{ph}^R = \lambda(T_R^4 - T_L^4), \quad (36)$$

where $\lambda \approx 2\pi^5 K^2 C^2 k_B^4 / (15\hbar)$, where K is the stiffness of the nano-structured object bridging the metal electrodes, and C is the slope of the surface phonon's dispersion function in long wave-length limit. The effect of the phonon's thermal current on refrigeration is described by a single parameter λ , which is determined by K and C .

Observed from the recent experiments [62], the stiffness K of the linear Pt atomic chains varies in a wide range of several orders of magnitudes. The reason for this experimental finding could be that the atomic chain is particularly stiff along the chain direction in a perfectly linear atomic chain; otherwise, the atomic chain could be weak and vulnerable to bending. The magnitude of phonon's thermal current is sensible to the detailed atomic geometries in the contact region and could be uncertain. The simplified weak link model allows us to use a single parameter λ to investigate the effect of phonon's thermal current on refrigeration.

To determine the impact of the phonon's thermal current (J_{ph}^R), we repeat similar discussions in the previous subsection for the thermoelectric nano-refrigerators. Correspondingly, the COP of the thermoelectric nano-refrigerator becomes

$$\eta^{el+ph} = \frac{J_{el+ph}^R}{IV_B}, \quad (37)$$

where $J_{el+ph}^R = J_{el}^R + J_{ph}^R$ is the combined thermal current.

We assume that $\Delta T \ll T_R$ and limit ourself to small bias regime ($V_B \ll 20$ mV) to avoid substantial local heating. In this case, Eq. (36) is reduced to,

$$J_{ph}^R \approx -4\lambda T_R^3 \Delta T. \quad (38)$$

Using Eqs. (27) and (38), the combined thermal current can be expressed in terms of a polynomial of V_B similar to Eq. (27),

$$J_Q^R = -a_{el+ph} + bV_B - cV_B^2 - dV_B^3, \quad (39)$$

where $a_{el+ph} = 2\pi^2 k_B^2 \tau(\mu) T_R \Delta T / (3h) - 4\lambda T_R^3 \Delta T$; the coefficients b , c , and d remain the same as those in Eq. (27).

An analogy can be drawn here between Eqs. (39) and (27), and likewise between Eqs. (37) and (25). Consequently, the discussions in the previous section can be easily replicated here. In the presence of phonon's thermal current, the working condition of the nano-refrigerator becomes,

$$-S > \sqrt{\left(\frac{2\pi^2 k_B^2}{3e^2} + \lambda \frac{8T_R^2}{\sigma}\right) \left(\frac{\Delta T}{T_R}\right)}, \quad (40)$$

where λ represents the strength of the phonon's thermal current, and σ is the conductance of the nanojunction. As the phonon's thermal current vanishes ($\lambda = 0$), Eq. (40) restores Eq. (28). Equation (40) shows that the phonon's thermal current is an adverse effect to thermoelectric refrigeration. A sufficiently large phonon's thermal current has a large value of λ , which is likely to break down the inequality described in Eq. (40) and ruin refrigeration capability.

For a given T_R and a given temperature difference ΔT , $J_Q^R(V_B)$ is a function of bias V_B . We note that J_Q^R is negative at $V_B = 0$; therefore, a minimum bias (denoted as V_{th}^{el+ph}) is needed to trigger possible thermoelectric cooling effect. The threshold bias V_{th}^{el+ph} is defined as the first zero of $J_{el}^R(V_B) = 0$. Owing to small value of V_{th}^{el+ph} and $\Delta T \ll T_R$, the threshold bias becomes

$$V_{th}^{el+ph} = V_{th}^{el} + \lambda [4(-S) T_R^2 \Delta T / \sigma], \quad (41)$$

where V_{th}^{el} is given by Eq. (29) which is analogous to Eq. (41). The threshold bias V_{th}^{el+ph} increases as the intensity of the phonon's thermal current (λ) increases.

Finally, we investigate the optimized value of the COP for a given T_R and a given temperature difference ΔT . The upper limit of COP considering the phonon's thermal current is given by

$$\eta_{\max}^{el+ph} = \left[(\eta_{\max}^{el})^{-1} + \lambda \left(\frac{16T_R \Delta T}{S^2 \sigma} \right) \right]^{-1}, \quad (42)$$

where $\eta_{\max}^{el}$ is the upper limit of COP given by Eq. (34) which is analogous to Eq. (42).

III. RESULTS AND DISCUSSION

The aim of this research is to investigate the novel thermoelectric cooling effect based on a thermoelectric junction at the atomic level. First-principles calculations and analytical theories are proposed in order to apply the quantum natures offered by the nano-structures to the function of thermoelectric nano-refrigerators. The atomic-scale thermoelectric junction is marked by the enhanced Seebeck coefficient due to reduced tunneling potential via bridging atoms, the suppressed local heating due to the nanoscale structure as well as small operation bias, and the suppressed photon radiation due to small size. Atomic-level control of the contact region could provide an alternative method to suppress the phonon's thermal current via weakened mechanical coupling between nano-structured object and electrodes. The above notable features suggest that the atomic-scale thermoelectric junctions as nano-refrigerators are worth examining.

A. Thermoelectric Properties of the 4-Al Atomic Junction

We propose a 4-Al junction as a thermoelectric cooling device, as depicted in Fig. 1(a). The aluminum junction is an ideal test bed for comparing quantum transport theories under non-equilibrium and experiments [58, 59]. The proposed 4-Al junction has a salient Seebeck effect due to the Px-Py orbital near the chemical potentials. The 4-Al thermoelectric junction serves as an examples illustrating the advantage of nano-scale refrigerators, where the overwhelmingly Joule heat in the bulk system and photon radiation are strongly suppressed due to size reduction. The phonon's thermal current, which is relevant to the mechanical elasticity of nanojunction, could also be suppressed by controlling the atomic contact region. These properties facilitate possible thermoelectric cooling in the 4-Al junction beyond the expectation of conventional solid-state device theory.

We begin our discussion by considering an ideal 4-Al atomic chain bridging two bulk Al metal electrodes that we model as ideal metals (jellium model, $r_s \approx 2$). The nano-structured object is considered in scattering approaches. The scattering wave functions of the whole system are calculated by solving the Lippmann-Schwinger equation iteratively until self-consistency is obtained. We assume that the left and right electrodes are independent electron and phonon reservoirs ($T_C = T_R$; $T_H = T_L = T_R + \Delta T$), respectively, with the electron and phonon population described

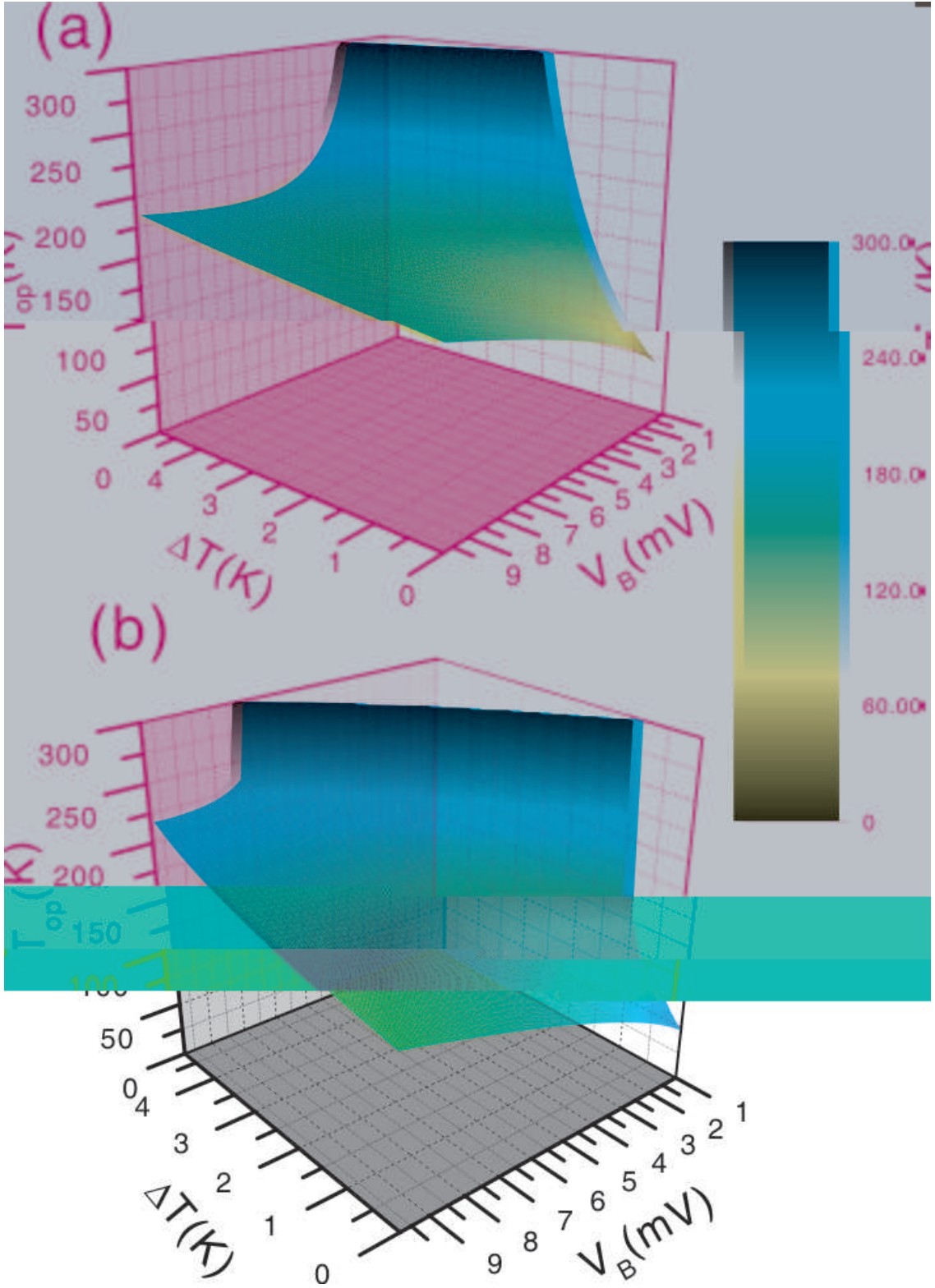


FIG. 2: (Color online) (a) Critical operation temperature T_{op} vs. ΔT and V_B in the absence of the phonon's thermal current; (b) T_{op} vs. ΔT and V_B in the presence of the phonon's thermal current with $\lambda = 10^{-17}$ Watt/K⁴.

by the Fermi-Dirac and Bose-Einstein distribution function. Two electrodes are connected to a battery with an applied bias $V_B = (\mu_R - \mu_L)/e$, where μ_L and μ_R are the chemical potential deep in the left and right electrodes, respectively. A detailed account of the theory is given in subsection **II. A Density Functional Theory**. The choice of thermoelectric junction with a large Seebeck coefficient is of crucial importance for the design of thermoelectricnanodevices. Therefore, we investigate the thermoelectric properties of the 4-Al atomic junction as follows.

The Seebeck coefficients are calculated from first-principles using the transmission function obtained from the DFT calculations, as described in Eq. (9). The 4-Al atomic junction is marked by a sigma channel near the chemical potentials with the Px-Py orbital characters, as shown in Fig. 1(b). The Seebeck coefficients correlate highly with the magnitudes and slopes of DOSs near the chemical potentials, as described in Eq. (11). The sigma channel leads to a large value in the slope of the transmission function near the chemical potentials. This is the reason for the enhanced Seebeck coefficient in the 4-Al atomic junction, as shown in Fig. 1(c), which compares favorably with those of Pt, Pd, and Au atomic chains.

The efficiency of energy conversion in the thermoelectric junction is usually characterized by the figure of merit (denoted as ZT), as defined in Eq. (23). ZT depends on the following physical factors: the Seebeck coefficient (S), the electric conductance (σ), the electron's thermal conductance (κ_{el}), and the phonon's thermal conductance (κ_{ph}). These physical factors can be evaluated using Eqs. (9), (18), (13), and (36), respectively. When ZT tends to infinity, the thermoelectric efficiency will reach the Carnot efficiency, the upper limit of energy conversion efficiency. To obtain a large ZT value, the thermoelectric nanojunction will require a large value of S , a large value of σ , and a small value of the combined heat conductance ($\kappa = \kappa_{el} + \kappa_{ph}$). Thermoelectric devices with a large value of σ are usually accompanied by a large value of κ_{el} , due to the same proportionality with the transmission function. These values are highly correlated, making the enhancement of the thermoelectric figure of merit ZT a challenging task.

The thermal energy carried by phonons flows from the hot into cold reservoir and is a negative effect to the thermoelectric refrigeration. We consider the rate of thermal energy carried by the phonon in the weak link model [as described in Eq. (19)], where each electrode is assumed to be in thermodynamic equilibrium, joined by a weak mechanical link modeled by a harmonic spring of stiffness K . In the weak-tunneling limit, the weak link model can be interpreted as an application of the thermal Landauer formula [60]. Up to the leading order in temperatures, we expand Eq. (19) which gives a simple form, $J_{ph}^R = \lambda(T_R^4 - T_L^4)$ [i.e., Eq. (36) specified as the simplified weak link model], where $\lambda \approx 2\pi^5 K^2 C^2 k_B^4 / (15\hbar)$. Simplification allows us to investigate the effect of the phonon's thermal current with a single parameter λ , which is determined by the stiffness of the nano-structured object (K) and the slope of the surface phonon's spectral density (C) in the electrodes. The simplified weak link model is valid for $T \ll T_D$, where $T_D = 394$ K is the Debye temperature for Al. We note that the simplified weak link model violates the Wiedemann-Franz law in low-temperature regime, while Eq. (19) restores the Wiedemann-Franz law at $T \gg T_D$. The range of temperatures discussed in this study lies within the valid regime of the simplified weak link model. Therefore, we consider ZT as a function of temperatures in the presence of the phonon's thermal current of which is represented by various values of λ , as shown in Fig. 1(d). The validity of the λ values for linear atomic wires will be justified later.

B. Thermoelectric Cooling Effect in the Absence of Phonon's Thermal Current

In the bulk system, the efficiency of a thermoelectric refrigerator is usually suppressed by the overwhelmingly irreversible Joule heating. Local heating in the nanojunction is analogous to Joule heating in the bulk system. Local heating arises from energy exchanged between the transport electrons and the vibration of the bridging nano-object. The heat generated in the nano-object via electron-vibration interaction is dissipated into electrodes, and is thus a negative effect to thermoelectric refrigeration. The amount of heat generated in the nanojunction depends on several factors, including the strength of electron-vibration interaction, background temperatures, and inelastic electron mean free path [22]. The nano-object bridging the junction is formed by few atoms, and thus the dispersion relation of phonon is characterized by the lack of Goldstone mode. When normal coordinates are considered, the complex vibrations of nano-object connecting to heavy electrodes can be cast into a set of independent simple harmonic oscillators described as normal modes. These features allow us to avoid the overwhelmingly irreversible heating effect by considering the 4-Al atoms junction operating under a bias much smaller than the onset bias V_{onset} (≈ 20 mV for 4-Al junction [61]), where eV_{onset} is the energy of the lowest normal mode and where the local heating is significantly suppressed.

The suppression of local heating due to the small probability for electron-vibration interactions comes from two perspectives. First, the distance between two electrodes is much smaller than the electron-phonon mean free path, and thus the probability for electrons with sufficient energy to excite the vibration of nano-structure is small. Second, the atomic junction is operated under a small bias ($V_B \ll V_{onset}$), and thus the majority of electrons have energies smaller than the lowest normal mode vibration of the nano-object connecting to the electrodes as a whole system,

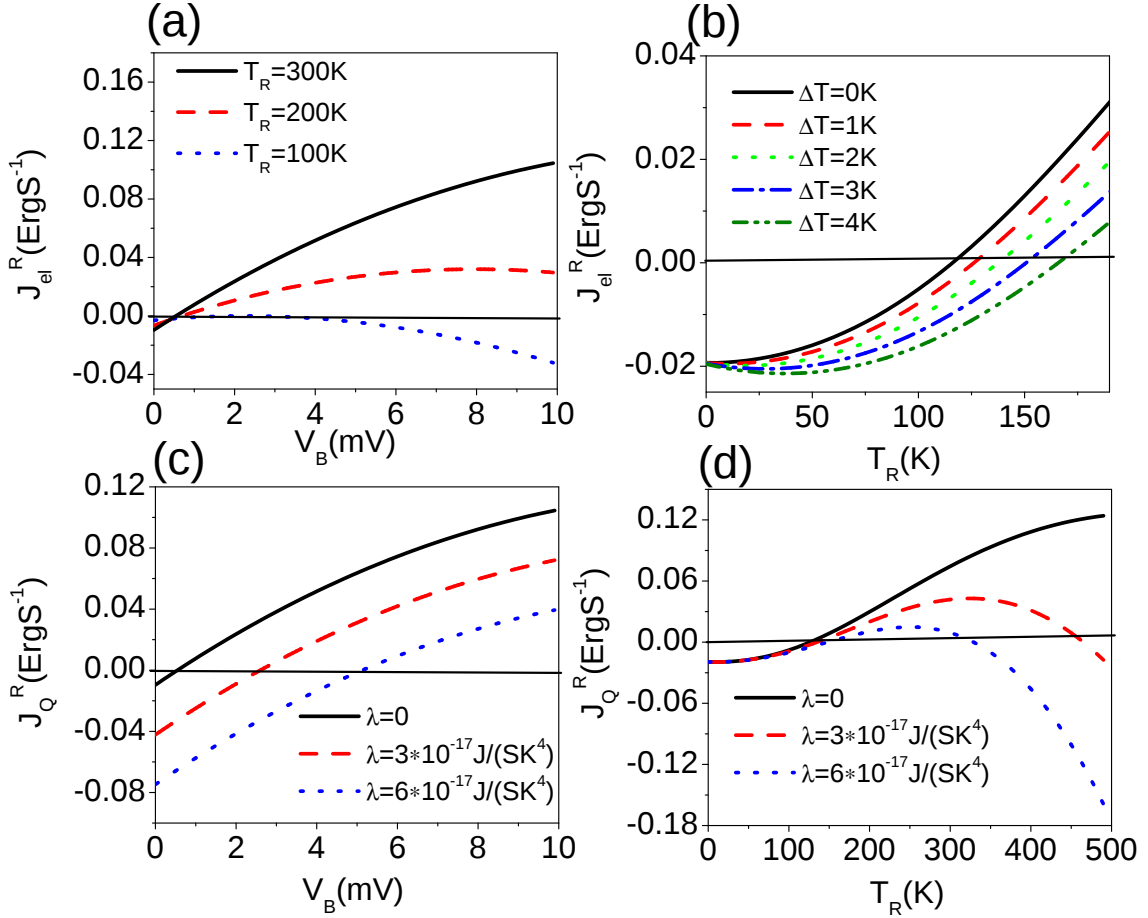


FIG. 3: (Color online) (a) J_{el}^R vs. V_B for various values of T_R in the absence of the phonon's thermal current, where $\Delta T = 1$ K; (b) J_{el}^R vs. T_R for various values of ΔT in the absence of the phonon's thermal current, where $V_B = 6$ mV; (c) J_Q^R vs. V_B in the presence of the phonon's thermal current for various values of λ , where $\Delta T = 1$ K and $T_R = 300$ K; and (d) J_Q^R vs. T_R in the presence of the phonon's thermal current for various values of λ , where $\Delta T = 1$ K and $V_B = 6$ mV.

apart from a small fraction of electrons that are thermally excited with energy larger than $\mu_R + eV_{onset}$ and due to the broadening effect.

The atomic refrigerator possesses another prominent advantage, the suppression of photon radiation. Photon radiation is proportional to the surface size of the metal contact according to Stefan's law. The reduced surface size of the metal electrodes in typical nanojunctions significantly suppresses the energy transport carried by the photon radiation. Consequently, the photovoltaic effect, which is also against the thermoelectric cooling, can be neglected.

The suppression of local heating and photon radiation due to size reduction remarkably facilitates the possible thermoelectric cooling effect in the 4-Al junctions beyond the expectation of the conventional bulk thermoelectric device theory. Our calculations indicate that as a thermoelectric nano-refrigerator, the 4-Al junction could work at temperatures below 100 K, which is a great improvement in comparison with the vacuum diode. In this regard, low operation temperature is an excellent characteristic of electronic nano-refrigerators.

Let us now attempt to investigate the 4-Al junction as a thermoelectric cooling device from the first-principles approaches. For the present, we shall confine our attention to the simplest case, the one which neglects the phonon's thermal current. The phonon's thermal current will be considered in the next subsection. We also put forward an analytical theory to explain the numerical results. The analytical theory described below is general to any atomic/molecular thermoelectric junction as a thermoelectric nano-refrigerator.

When external bias is applied, electrons flow from the right to the left electrodes. The flow of electrons carries not only the charge current but also the energy current. The thermal current carried by electrons [denoted as $J_{el}^{R(L)}(\mu_L, T_L; \mu_R, T_R)$], defined as the rate at which thermal energy flows from the right (into the left) electrode, can be calculated from first-principles using Eq. (7) with the help of the wavefunctions obtained self-consistently in the DFT calculations. Note that $J_{el}^R + IV_B = J_{el}^L$ [for details see Eq. (24)] because of energy conservation. It implies that

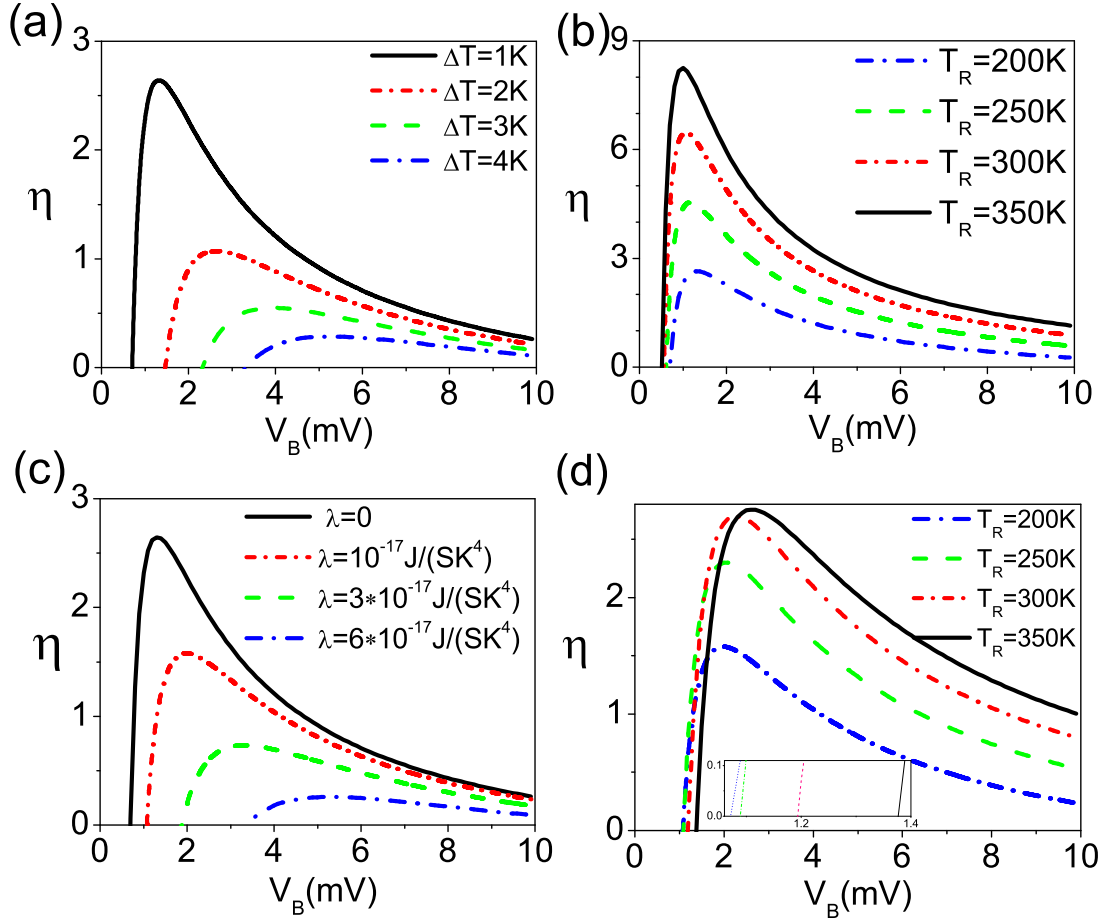


FIG. 4: (Color online) (a) COP (η) vs. V_B in the absence of the phonon's thermal current for various values of ΔT , where $T_R = 200$ K; (b) η vs. V_B in the absence of the phonon's thermal current for various values of T_R , where $\Delta T = 1$ K; (c) η vs. V_B in the presence of the phonon's thermal current for various values of λ , where $T_R = 200$ K and $\Delta T = 1$ K; and (d) η vs. V_B for various values of T_R in the presence of phonon's thermal current, where $\Delta T = 1$ K and $\lambda = 10^{-17}$ J/(sec-K⁴). The enlarged graph (inset) shows that the zeros of COP (i.e., V_{th}^{el+ph}) increases as T_R increases.

the thermoelectric refrigeration requires electric power IV_B to remove thermal energy from the cold (right) reservoir (with rate J_{el}^R) and reject waste thermal energy to the hot (left) reservoir (with rate J_{el}^R). The nano-refrigerator works when $J_{el}^R > 0$. As noted in Eq. (7), J_{el}^R is a function of V_B , ΔT , and T_R . At a given V_B and ΔT , the solution of $J_{el}^R(T_R) = 0$ defines the threshold operation temperature, denoted as T_{op} , below which the nano-refrigerator does not function. Figure 2(a) shows the T_{op} of the 4 – Al nano-refrigerator as a function of ΔT and V_B . The operating temperature of the 4 – Al nano-refrigerator can be lower than 100 K, as shown in Fig. 2(a).

To enrich the understanding of thermoelectric nano-refrigerators, we also propose analytical theories that provide guidelines for the design of nano-refrigerators. When $\Delta T \ll T_R$, the application of the Sommerfeld expansion on Eq. (7) can simplify the electron's thermal current as a polynomial of V_B , as described in Eq. (27). If the higher-order term V_B^3 is neglected, the maximum of $J_{el}^R(T_R)$ that is greater than zero yields a criterion for the existence of thermoelectric cooling, which gives Eq. (28): $-S > \pi k_B \sqrt{2\Delta T / (3T_C)} / e$, where $T_C (= T_R)$ is the temperature of the cold (right) reservoir, $S = -\pi^2 k_B^2 \tau'(\mu) T_R / [3e\tau(\mu)]$ is the Seebeck coefficient, k_B is the Boltzmann constant, and e is the electron charge. To have possible refrigeration effect, the Seebeck coefficient S , the temperature difference ΔT , and the temperature of the cold reservoir T_C need to satisfy Eq. (28). The choice of an n-type thermoelectric junction with a large Seebeck coefficient is of crucial importance in the design of thermoelectric nano-refrigerators. Large Seebeck coefficients could be achieved through an appropriate choice of bridging nano-structured objects and further optimized by applying gate voltages [39, 48].

Figure 3(a) shows the rate of thermal energy extracted from the cold temperature reservoir (J_{el}^R) as a function of

V_B for $T_R = 100, 200$, and 300 K, where the temperature difference between the hot and cold reservoir ΔT is fixed at 1 K. We note that $J_{el}^R < 0$ at zero bias[see Fig. 3(a)], and thus a threshold voltage V_{th}^{el} for the battery is needed to trigger the refrigeration effect. The threshold bias is defined as the smallest positive solution of $J_{el}^R(V_B) = 0$ for a given T_R and ΔT . When $V_B < V_{th}^{el}$, the rate of thermal energy removed from the cold reservoir is negative ($J_{el}^R < 0$) and thus the thermoelectric nano-refrigerator does not function. Since V_{th}^{el} has a very small value, we neglect the terms higher than the first order of V_B in Eq. (27) and obtain V_{th}^{el} from $J_{el}^R(V_B) = 0$, as described in Eq. (29), where we assumed $\Delta T \ll T_R$. Equation (29) predicts that the threshold voltage $V_{th}^{el} = -\pi^2 k_B^2 \Delta T / (3e^2 S)$ is independent of T_R , as shown in Fig. 3(a).

Figure 3(b) shows J_{el}^R as a function of T_R for different values of $\Delta T = 0, 1, 2, 3$, and 4 K, where the bias is fixed at $V_B = 6$ mV. For a given V_B and ΔT , we define the critical operation temperature as the solution of $J_{el}^R(T_R) = 0$. The thermoelectric nano-refrigerator is working when $T_R > T_{op}$. The critical operation temperature can be calculated from Eq. (26): $T_{op} \approx \frac{1}{2}[(\alpha - 1)\Delta T + \sqrt{(\alpha^2 - 1)\Delta T^2 + \beta}]$, where $\alpha = \tau(\mu_L)/[\tau'(\mu_L)eV_B]$ and $\beta = -2V_B/S$. The foregoing equation predicts that T_{op} increases as ΔT increases, which agrees well with the numerical calculation presented in Fig. 3(b). If $\Delta T = 0$, then T_{op} reaches the minimum value $(T_{op})_{\min} \approx \sqrt{T_R V_B / (-2S)}$ as described in Eq. (31). The equation shows that $(T_{op})_{\min}$ increases as V_B increases and $(T_{op})_{\min}$ increases as T_R increases, respectively. At $V_B = 6$ mV, the $(T_{op})_{\min}$ for the $4 - Al$ thermoelectric refrigerator is 116 K, which can be further suppressed by decreasing the bias V_B .

Turning to the coefficient of performance of the thermoelectric nano-refrigerator, the COP (denoted as η^{el}) is defined as the ratio of the rate of heat removed from the cold reservoir to the electric power supplied by the battery, that is, $\eta^{el} = J_{el}^R / IV_B$, as equivalent to Eq. (32). Derived from Eq. (33), the maximum value of COP is given by Eq. (34). Figure 4(a) shows the numeric calculations of η^{el} as a function of V_B for $\Delta T = 1, 2, 3$, and 4 K, where $T_R = 200$ K. Figure 4(b) shows the numeric calculations of η^{el} as a function of V_B for $T_R = 150, 200, 250$, and 300 K, where $\Delta T = 1$ K. The exchange of energy by heat currents between the hot and cold reservoirs is an irreversible process, and leads the decrease of the COP as ΔT increases, as shown in Fig. 4(a). This also agrees well with the prediction of Eq. (34).

The maximum value of COP (denoted as $\eta_{\max}^{el}$) occurs at bias $V_{\max}^{\eta} \approx 2V_{th}^{el}$, where V_{th}^{el} is the threshold bias for possible refrigeration given by Eq. (29): $\eta_{\max}^{el} = 3e^2 S^2 T_R / (4\pi^2 k_B^2 \Delta T) - 1/2$. As a direct consequence of the above equation, the maximum value of COP ($\eta_{\max}^{el}$) increases as $S^2 T_R$ increases and decreases as ΔT increases. Remarkably, $V_{\max}^{\eta}$ is independent of T_R as shown in Figs. 4(a) and 4(b). This result also agrees well with the theoretical prediction because $V_{\max}^{\eta} \approx 2V_{th}^{el}$ and V_{th}^{el} is independent of T_R as described in Eq. (29). We should note that the maximum value of COP can be greatly enhanced by a suitable nanojunction with a large Seebeck coefficient according to $\eta_{\max}^{el} \propto S^2$ as predicted in Eq. (34). Our study demonstrates that by taking advantage of the quantum features of reduced dimensions, a nano-refrigerator with a figure of merit $ZT \approx 0.02$ has a COP comparable to a conventional TE refrigerator with a $ZT \approx 0.2$.

C. Thermoelectric Cooling Effect Including the Phonon's Thermal Current

The phonon's thermal current carries thermal energy from the hot to cold reservoir, which is an adverse effect to refrigeration. To assess the extent of this adverse effect, we consider the phonon's thermal current within the simplified weak link model. The simplified weak link model is suitable for describing the heat transport for two thermal reservoirs connected by a weak elastic link in a low temperature regime ($T \ll T_D$) and is convenient to describe the phonon's thermal current by a single parameter λ : $J_{ph}^R = \lambda(T_R^4 - T_L^4)$, where $\lambda \approx 2\pi^5 K^2 C^2 k_B^4 / (15\hbar)$. The parameter λ can be determined by K and C , where K is the stiffness of the nano-structured object and C is the slope of the spectral density $N(E) \approx C \times E$. From recent experiments [62], it is observed that the stiffness of the linear Pt atomic chains varies in a wide range of several orders of magnitudes. This experiment suggests that the stiffness K is likely to depend strongly on the detailed atomic structure of the full system, especially in the contact region. For example, the atom chain could be particularly stiff along the chain direction when the atomic chain forms a perfectly straight line; otherwise, the atomic (zigzag) chain could easily bend with much smaller stiffness. In this view, the magnitude of phonon's thermal current could possibly exist in a wide range of magnitudes in a nanojunction formed by a monatomic chain. An estimation from the experimental data of K and C in the Pt atomic junction yields the values of λ range to be from 0 to 2.05×10^{-19} W/K⁴ in a typical atomic chain [62, 63]. The simplified weak link model allows the construction of an analytical theory that offers a concise explanation for how the phonon's thermal current (represented by a single parameter λ) affects thermoelectric cooling. We choose λ , which may not be underestimated, around the order of 10^{-17} W/K⁴ to compare with the value of Pt atomic junction. An alternative reason for choosing the λ values around the order of 10^{-17} W/K⁴ to present the phonon's thermal current is that thermoelectric refrigeration is sensitive with λ around the order of 10^{-17} W/K⁴ as shown below.

The COP in the presence of the phonon's thermal current J_{ph}^R is defined as $\eta = \frac{J_Q^R}{T_V}$, where $J_Q^R = J_{el}^R + J_{ph}^R$ is the combined thermal current. In the presence of the phonon's thermal current, the functioning of the 4-Al atomic refrigerator requires higher operation temperatures, as shown in Fig. 2(b), where we plot the operation temperature T_{op} as a function of V_B and ΔT with $\lambda = 10^{-17}$ W/K⁴. Applying the Sommerfeld expansion, the combined thermal current J_Q^R can be expressed as a polynomial of V_B when $\Delta T \ll T_R$, as described in Eq. (39). When the term V_B^3 is neglected in Eq. (39), the criterion for the existence of electronic cooling is given by Eq. (40), derived from the condition that the maximum value of J_Q^R is positive. The criterion for possible thermoelectric refrigeration [Equation (40)] provides the guideline for devising experiments to test the effect of thermoelectric cooling at the atomic level. When $\lambda \rightarrow 0$, Eq. (40) restores Eq. (28) in the absence of the phonon's thermal current.

Figure 3(c) shows the combined thermal current J_Q^R as a function of V_B for $\lambda = 0, 3 \times 10^{-17}$ W/K⁴, and 6×10^{-17} W/K⁴, where we fix $\Delta T = 1$ K and $T_R = 300$ K. Note that $J_Q^R < 0$ at zero bias. Similar to the previous discussions in the absence of the phonon's thermal current, the thermoelectric nano-refrigerator works when $J_Q^R > 0$. This leads to a threshold voltage [$V_{th}^{el+ph} = V_{th}^{el} + \lambda [4(-S)T_R^2\Delta T/\sigma]$, as given in Eq. (41)], which is the minimum external bias required to trigger the thermoelectric refrigeration. Equation (41) predicts that the threshold bias (V_{th}^{el+ph}) increases as λ increases, which agrees well with the numerical calculations as shown in Fig. 3(c). Figure 3(d) shows the combined thermal current J_Q^R as a function of T_R for $\lambda = 0, 3 \times 10^{-17}$ W/K⁴, and 6×10^{-17} W/K⁴, where we fix $V_B = 6$ mV and $\Delta T = 1$ K. Figure 3(d) exhibits the combined thermal current J_Q^R , which could become negative at high temperatures regime. The reason for this is that the phonon's thermal current brings heat from the hot to the cold reservoir. Thus, the combined thermal current becomes a negative value, which disables refrigeration capability at high temperatures. This imposes an upper limit for the working temperature, above which J_Q^R turns to be negative and consequently the nano-refrigerator does not function.

Derived from Eq. (39), the upper limit of COP (denoted as $\eta_{\max}^{el+ph}$) is given by Eq. (42): $\eta_{\max}^{el+ph} = \left[(\eta_{\max}^{el})^{-1} + \lambda (16T_R\Delta T/(S^2\sigma)) \right]^{-1}$. Equation (42) predicts that $\eta_{\max}^{el+ph}$ decreases as $T_R\Delta T$ increases and $\eta_{\max}^{el+ph}$ increases as $S^2\sigma$ decreases. In Fig. 4(c), we show the numeric calculations of the COP (η^{el+ph}) as a function of V_B in the presence of the phonon's thermal current represented by $\lambda = 0, 1 \times 10^{-17}, 3 \times 10^{-17}, 6 \times 10^{-17}$ W/K⁴, where we fix $\Delta T = 1$ K and $T_R = 200$ K. Figure 4(c) shows that the upper limit of COP ($\eta_{\max}^{el+ph}$) decreases as the strength of phonon's thermal current increases because the phonon's thermal current is an adverse effect to refrigeration. Figure 4(c) also shows that V_{th}^{el+ph} increases as λ increases and agrees well with the prediction of Eq. (41). Figure 4(d) shows the numeric calculations of the COP (η^{el+ph}) as a function of V_B for $T_R = 200, 250, 300$, and 350 K, where we fix $\Delta T = 1$ K and $\lambda = 1 \times 10^{-17}$ W/K⁴. As shown in Fig. 4(d), the upper limit of COP ($\eta_{\max}^{el+ph}$) increases as λ increases as predicted by Eq. (42); meanwhile, the inset of Fig. 4(d) shows that the V_{th}^{el+ph} increases as T_R increases, as predicted by Eq. (41) when $\Delta T \ll T_R$.

The phonon's thermal current, which is relevant to the mechanical coupling between the nano-structured object and the electrodes, is an adverse effect to refrigeration. To minimize the adverse effects, we suggest creating a weak mechanical link between the nano-structured object and the electrodes while still allowing electrons to tunnel.

IV. CONCLUSIONS

In theory, we propose an innovative idea for finding a possible thermoelectric cooling device at the atomic scale. In-depth research from the first-principles approaches is performed to investigate the thermoelectric cooling effect of the atomic-scale refrigerator. This research offers a key to understanding the energy-conversion mechanism at the atomic scale. Our studies show that the choice of thermoelectric junction with a large Seebeck coefficient is of crucial importance for the design of thermoelectric nano-devices. The bridging Al atoms create potential wells that lead to resonant tunneling via a sigma channel near the chemical potentials with the Px-Py orbital characters, and thus significantly enhance the Seebeck coefficient of the 4-Al atomic junction.

When the nano-refrigerator is operated under a bias smaller than the onset voltage ($V_B \ll V_{onset}$), the local heating is significantly suppressed. Our research shows that the suppression of local heating, photon radiation and tunneling barrier by the bridging atoms in nanojunction is favorable for the operation of thermoelectric nano-refrigerators. The meritorious factors mentioned above remarkably facilitate thermoelectric cooling beyond the expectation of the conventional thermoelectric device theory in the bulk system.

Analytical theories have been established to offer a more elaborate explanation of the working conditions, threshold bias, and properties of coefficient of performance. We observe a threshold bias V_{th} below which no refrigeration is possible. The COP of nano-refrigerators is optimized at $V_B \approx 2V_{th}^{el}$ when $\Delta T \ll T_R$. A major adversary factor to thermoelectric refrigeration is the phonon's thermal current, which is likely to depend strongly on the detailed atomic

structure of the full system, especially in the contact region. To minimize the adverse effect of the phonon's thermal current, we suggest creating a failure in the mechanic link between the nano-structured object and the electrodes, while still allowing the electrons to tunnel.

This research has theoretically revealed that an atomic-scale thermoelectric refrigerator is promising. The nano-refrigerators potentially have COP comparable to conventional TE refrigerators with ZT , which is an order of magnitude larger. Moreover, widely diversified atomic-sized junctions may be achieved by manipulating the species of nano-structured objects and the contact region. Such manipulations may lead to a significant change in the DOSs and the stiffness of nanojunction, consequently varying the Seebeck coefficients and the phonon's thermal current. Atomic-level control of the contact region is expected to open new opportunities and challenges in developing new forms of thermoelectric energy conversion devices, which need to be extended by the utilization of unprecedented experiments. We hope that our forward-looking theoretical proposal could stimulate innovated experiment towards further exploration of atomic/molecular system which may lead to practical applications of nanoscale thermoelectric cooling devices in the future.

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- ¹ A. Aviram and M. A. Ratner, Chem. Phys. Lett. **29**, 277 (1974).
 - ² M. Di Ventra, *Electrical transport in nanoscale systems*, (Cambridge University Press, Cambridge, 2008).
 - ³ C. C. Kaun and H. Guo, Nano Lett. **3**, 1521 (2003).
 - ⁴ M. Di Ventra and N. D. Lang, Phys. Rev. B **65**, 045402 (2001).
 - ⁵ A. Nitzan and M. A. Ratner, Science **300**, 1384 (2003).
 - ⁶ M. Kamenetska, S. Y. Quek, A. C. Whalley, M. L. Steigerwald, H. J. Choi, S. G. Louie, C. Nuckolls, M. S. Hybertsen, J. B. Neaton, and L. Venkataraman, J. Am. Chem. Soc. **132**, 6817 (2010).
 - ⁷ G. C. Solomon, C. Herrmann, T. Hansen, V. Mujica, and M. A. Ratner, Nature Chemistry **2**, 223 (2010).
 - ⁸ W. Wang, T. Lee, I. Kretzschmar, and M. A. Read, Nano Lett. **4**, 643 (2004).
 - ⁹ M. Galperin, A. Nitzan, and M. A. Ratner, Phys. Rev. B **78**, 125320 (2008).
 - ¹⁰ J. Jiang, M. Kula, W. Lu, and Y. Luo, Nano Lett. **5**, 1551 (2005).
 - ¹¹ L. H. Yu, C. D. Zangmeister, J. G. Kushmerick, Phys. Rev. Lett. **98**, 206803 (2007).
 - ¹² M. Paulsson, T. Frederiksen, and M. Brandbyge, Nano Lett. **6**, 258 (2006).
 - ¹³ G. C. Slomon, A. Gagliardi, A. Pecchia, T. Frauenheim, A. Di Carlo, J. R. Reimers, and N. S. Noel, J. Chem. Phys. **124**, 094704 (2006).
 - ¹⁴ Y. C. Chen, M. Zwolak, and M. Di Ventra, Nano Lett. **5**, 621 (2005).
 - ¹⁵ Y. C. Chen, Phys. Rev. B **78**, 233310 (2008).
 - ¹⁶ I. S. Kristensen, M. Paulsson, K. S. Thygesen, and K. W. Jacobsen, Phys. Rev. B **79**, 235411 (2009).
 - ¹⁷ D. Djukic and J. M. van Ruitenbeek, Nano Lett. **6**, 789 (2006).
 - ¹⁸ M. Kiguchi, O. Tal, S. Wohlthat, F. Pauly, M. Krieger, D. Djukic, J. C. Cuevas, and J. M. van Ruitenbeek, Phys. Rev. Lett. **101**, 046801 (2008).
 - ¹⁹ P. J. Wheeler, J. N. Russom, K. Evans, N. S. King, and D. Natelson, Nano Lett. **10**, 1287 (2010).
 - ²⁰ Y. C. Chen and M. Di Ventra, Phys. Rev. Lett. **95**, 166802 (2005).
 - ²¹ Y. S. Liu and Y. C. Chen, cond-mat/arXiv:1005.3407.
 - ²² Y. C. Chen, M. Zwolak, and M. Di Ventra, Nano Lett. **3**, 1691 (2003).
 - ²³ Z. Huang, B. Xu, Y. C. Chen, M. Di Ventra, and N. J. Tao, Nano Lett. **6**, 1240 (2006).
 - ²⁴ M. Di Ventra, S. T. Pantelides, and N. D. Lang, Appl. Phys. Lett. **76**, 3448 (2000).
 - ²⁵ C. L. Ma, D. Nghiem, and Y. C. Chen, Appl. Phys. Lett. **93**, 222111 (2008).
 - ²⁶ P. M. Solomon and N. D. Lang, ACS Nano **2**, 435 (2008).
 - ²⁷ N. D. Lang and P. M. Solomon, ACS Nano **3**, 1437 (2009).
 - ²⁸ H. Song, Y. Kim, Y. H. Jang, H. Jeong, M. A. Reed, and T. Lee, Nature **462**, 1039 (2009).
 - ²⁹ C. H. Ahn, A. Bhattacharya, M. Di Ventra, J. N. Eckstein, C. D. Frisbie, M. E. Gershenson, A. M. Goldman, I. H. Inoue, J. Mannhart, A. J. Millis, A. F. Morpurgo, D. Natelson, and J. M. Triscone, Rev. Mod. Phys. **78**, 1185 (2006).
 - ³⁰ S. M. Lindsay and M. A. Ratner, Advanced Materials **19**, 23 (2007).
 - ³¹ N. J. Tao, Nat. Nanotechnol. **1**, 173 (2006).
 - ³² B. Ludoph and J. M. van Ruitenbeek, Phys. Rev. B **59**, 12290 (1999).
 - ³³ P. Reddy, S. Y. Jang, R. A. Segalman, and A. Majumdar, Science **315**, 1568 (2007).
 - ³⁴ K. Baheti, J. A. Malen, P. Doak, P. Reddy, S. Y. Jang, T. D. Tilley, A. Majumdar, and R. A. Segalman, Nano Lett. **8**, 715 (2008).
 - ³⁵ J. A. Malen, P. Doak, K. Baheti, T. D. Tilley, R. A. Segalman, and A. Majumdar, Nano Lett. **9**, 1164 (2009).
 - ³⁶ J. A. Malen, S. K. Yee, A. Majumdar, and R. A. Swgalman, Chem. Phys. Lett. **491**, 109 (2010).
 - ³⁷ M. Paulsson and S. Datta, Phys. Rev. B **67**, 241403(R) (2003).
 - ³⁸ X. Zheng, W. Zheng, Y. Wei, Z. Zeng, and J. Wang, J. Chem. Phys. **121**, 8537 (2004).

- ³⁹ B. Wang, Y. Xing, L. Wan, Y. Wei, and J. Wang, Phys. Rev. B **71**, 233406 (2005).
- ⁴⁰ F. Pauly, J. K. Viljas, and J. C. Cuevas, Phys. Rev. B **78**, 035315 (2008).
- ⁴¹ M. Galperin, A. Nitzan, and M. A. Ratner, Molecular Phys. **106**, 397 (2008).
- ⁴² Y. Dubi and M. Di Ventra, Nano Lett. **9**, 97 (2009).
- ⁴³ T. Markussen, A. P. Jauho, and M. Brandbyge, Phys. Rev. Lett. **103**, 055502 (2009).
- ⁴⁴ S. H. Ke, W. Yang, S. Curtarolo, and H. U. Baranger, Nano Lett. **9**, 1011 (2009).
- ⁴⁵ C. M. Finch, V. M. García-Suárez, and C. J. Lambert, Phys. Rev. B **79**, 033405 (2009).
- ⁴⁶ T. Markussen, A. P. Jauho, and M. Brandbyge, Phys. Rev. B **79**, 035415 (2009).
- ⁴⁷ J. P. Bergfield and C. A. Stafford, Nano Lett. **9**, 3072 (2009).
- ⁴⁸ Y. S. Liu and Y. C. Chen, Phys. Rev. B **79**, 193101 (2009).
- ⁴⁹ Y. S. Liu, Y. R. Chen, and Y. C. Chen, ACS Nano **3**, 3497 (2009).
- ⁵⁰ Y. Dubi and M. Di Ventra, Phys. Rev. B **79**, 081302(R) (2009).
- ⁵¹ M. Galperin, K. Saito, A. V. Balatsky, and A. Nitzan, Phys. Rev. B **80**, 115427 (2009).
- ⁵² Y. S. Liu, H. T. Yao, and Y. C. Chen, cond-mat/arXiv:1001.0822.
- ⁵³ G. D. Mahan, J. Appl. Phys. **76**, 4362(1994).
- ⁵⁴ G. D. Mahan and L. M. Woods, Phys. Rev. Lett. **80**, 4016 (1998).
- ⁵⁵ K. A. Chao, M. Larsson, and A. G. Mal'shukov, Appl. Phys. Lett. **87**, 022103 (2005).
- ⁵⁶ M. F. O'Dwyer, R. A. Lewis, C. Zhang, and T. E. Humphrey, Phys. Rev. B **72**, 205330 (2005).
- ⁵⁷ T. L. Westover and T. S. Fisher, Phys. Rev. B **77**, 115426 (2008).
- ⁵⁸ J. C. Cuevas, A. Levy Yeyati, A. Martín-Rodero, G. R. Bollinger, C. Untiedt, and N. Agraït, Phys. Rev. Lett. **81**, 2990(1998).
- ⁵⁹ K. S. Thygesen and K. W. Jacobsen, Phys. Rev. Lett. **91**, 146801 (2003).
- ⁶⁰ K. R. Patton and M. R. Geller, Phys. Rev. B **64**, 155320 (2001).
- ⁶¹ Z. Yang, M. Chshiev, M. Zwolak, Y. C. Chen, and M. Di Ventra, Phys. Rev. B **71**, 041402(R) (2005).
- ⁶² T. Shiota, A. I. Mares, A. M. C. Valkering, T. H. Oosterkamp, and J. M. van Ruitenbeek, Phys. Rev. B **77**, 125411 (2008).
- ⁶³ K. Kern, R. David, R. L. Palmer, G. Comsa, and T. S. Rahman, Phys. Rev. B **33**, 4334(R) (1986).
- ⁶⁴ N. D. Lang, Phys. Rev. B **52**, 5335 (1995).
- ⁶⁵ Y. C. Chen and M. Di Ventra, Phys. Rev. B **67**, 153304 (2003).